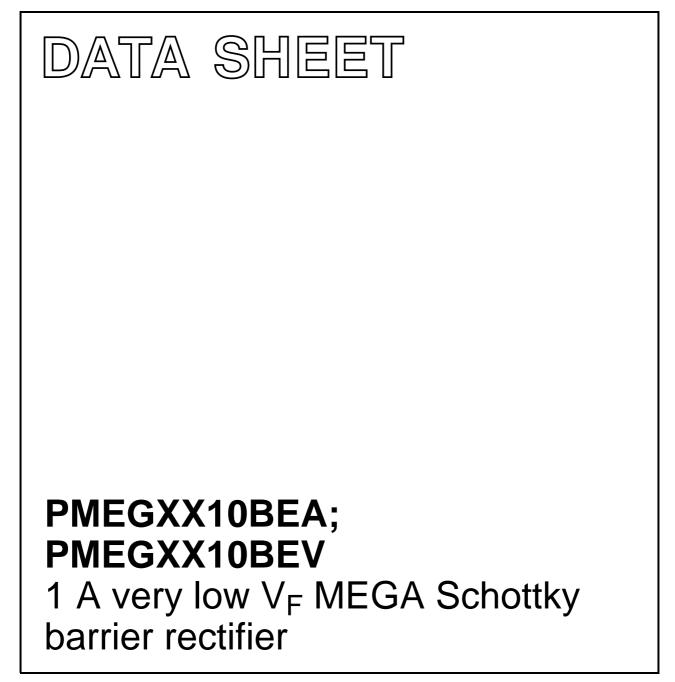
DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 2004 Apr 02 2004 Jun 14



PMEGXX10BEA; PMEGXX10BEV

1 A very low V_F MEGA Schottky barrier rectifier

FEATURES

- Forward current: 1 A
- Reverse voltages: 20 V, 30 V, 40 V
- Very low forward voltage
- Ultra small and very small plastic SMD package
- Power dissipation comparable to SOT23.

APPLICATIONS

- High efficiency DC-to-DC conversion
- Voltage clamping
- Protection circuits
- Low voltage rectification
- Blocking diodes
- Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a very small SOD323 (SC-76) and ultra small SOT666 SMD plastic package.

MARKING

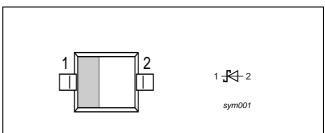
TYPE NUMBER	MARKING CODE			
PMEG2010BEA	V1			
PMEG3010BEA	V2			
PMEG4010BEA	V3			
PMEG2010BEV	G6			
PMEG3010BEV	G5			
PMEG4010BEV	G4			

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
l _F	forward current	1	А
V _R	reverse voltage	20; 30; 40	V

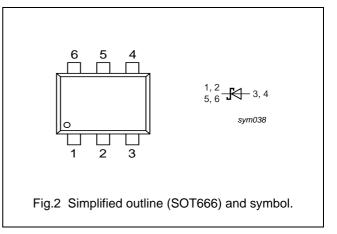
PINNING

PIN	DESCRIPTION			
PMEGXX10BEA (see Fig.1)				
1	cathode			
2	anode			
PMEGXX10BEV (see Fig.2)				
1, 2, 5, 6	cathode			
3, 4	anode			



The marking bar indicates the cathode.

Fig.1 Simplified outline (SOD323; SC-76) and symbol.



PMEGXX10BEA; PMEGXX10BEV

ORDERING INFORMATION

	NAME DESCRIPTION VERS		VERSION
PMEGXX10BEA	 plastic surface mounted package; 2 leads SOD32 		SOD323
PMEGXX10BEV		plastic surface mounted package; 6 leads	SOT666

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _R	continuous reverse voltage				
	PMEG2010BEA/PMEG2010BEV		_	20	V
	PMEG3010BEA/PMEG3010BEV		_	30	V
	PMEG4010BEA/PMEG4010BEV		_	40	V
I _F	continuous forward current	$T_s \le 55 \text{ °C}$; note 1	_	1	А
I _{FRM}	repetitive peak forward current	$t_p \le$ 1 ms; $\delta \le$ 0.5; note 2	-	3.5	А
I _{FSM}	non-repetitive peak forward current	t _p = 8 ms; square wave; note 2	-	10	A
Tj	junction temperature	note 3	_	150	°C
T _{amb}	operating ambient temperature	note 3	-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

Notes

- 1. Refer to SOD323 (SC-76) and SOT666 standard mounting conditions.
- 2. Only valid if pins 3 and 4 are connected in parallel (SOT666 package).
- 3. For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.

PMEGXX10BEA; PMEGXX10BEV

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
PMEGXX10BEA	(SOD323)	·		
R _{th(j-a)}	thermal resistance from junction to	in free air; notes 1 and 2	450	K/W
	ambient	in free air; notes 2 and 3	210	K/W
R _{th(j-s)}	thermal resistance from junction to soldering point	note 4	90	K/W
PMEGXX10BEV	(SOT666)	-		
R _{th(j-a)}	thermal resistance from junction to	in free air; notes 2 and 5	405	K/W
	ambient	in free air; notes 2 and 6	215	K/W
R _{th(j-s)}	thermal resistance from junction to soldering point	note 4	80	K/W

Notes

- 1. Refer to SOD323 (SC-76) standard mounting conditions.
- 2. For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses. Nomograms for determining the reverse power losses P_R and $I_{F(AV)}$ rating will be available on request.
- 3. Device mounted on an FR4 printed-circuit board with copper clad 10×10 mm.
- 4. Solder point of cathode tab.
- 5. Refer to SOT666 standard mounting conditions.
- 6. Only valid if pins 3 and 4 are connected in parallel (SOT666 package).

CHARACTERISTICS

 $T_{amb} = 25 \ ^{\circ}C$ unless otherwise specified.

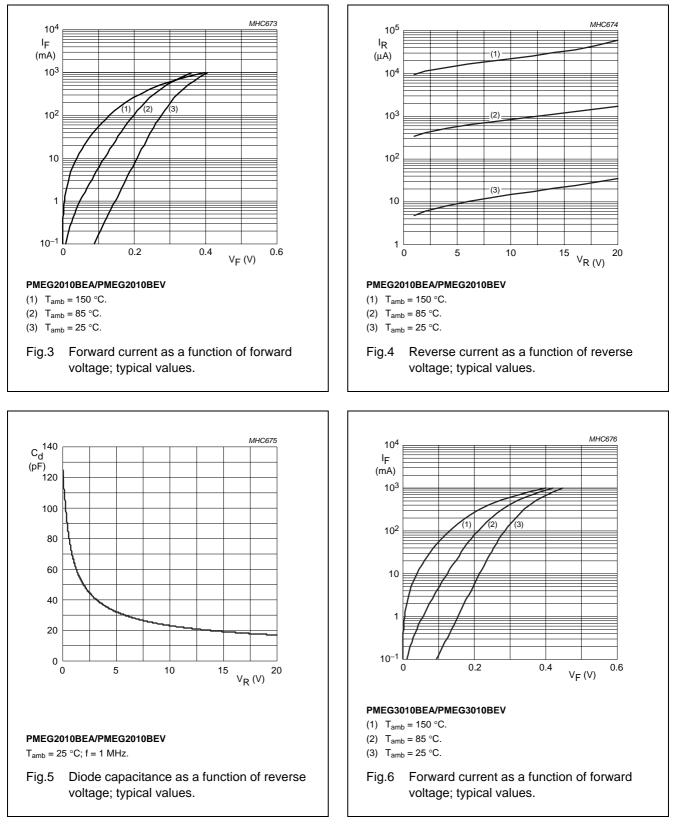
SYMBOL	PARAMETER	CONDITIONS	PMEG2010BEA/ PMEG2010BEV		PMEG3010BEA/ PMEG3010BEV		PMEG4010BEA/ PMEG4010BEV		UNIT
			TYP.	MAX.	TYP.	MAX.	TYP.	MAX.	
V _F	forward voltage	I _F = 0.1 mA	90	130	90	130	95	130	mV
		I _F = 1 mA	150	190	150	200	155	210	mV
		I _F = 10 mA	210	240	215	250	220	270	mV
		I _F = 100 mA	280	330	285	340	295	350	mV
		I _F = 500 mA	355	390	380	430	420	470	mV
		I _F = 1000 mA	420	500	450	560	540	640	mV
I _R	continuous	V _R = 10 V; note 1	15	40	12	30	7	20	μA
	reverse current	V _R = 20 V; note 1	40	200	_	_	_	-	μA
		V _R = 30 V; note 1	-	-	40	150	-	-	μA
		V _R = 40 V; note 1	-	-	-	-	30	100	μA
C _d	diode capacitance	V _R = 1 V; f = 1 MHz	66	80	55	70	43	50	pF

Note

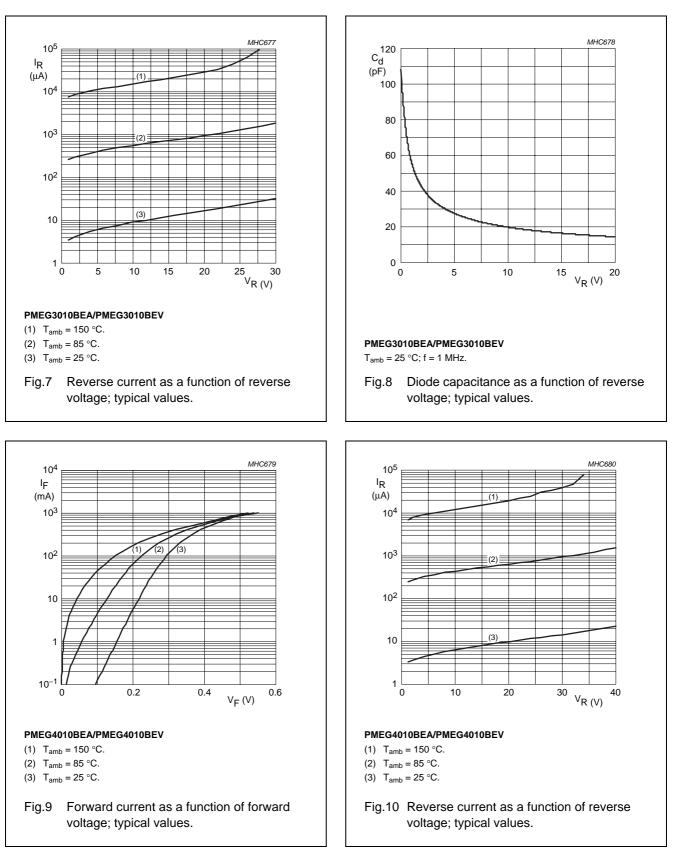
1. Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

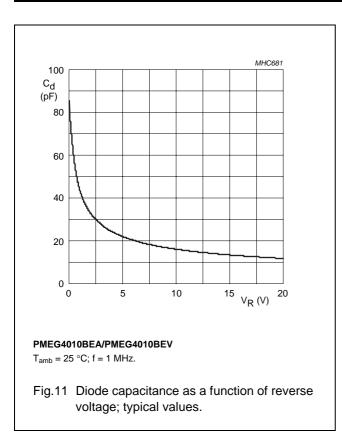
PMEGXX10BEA; PMEGXX10BEV

GRAPHICAL DATA



PMEGXX10BEA; PMEGXX10BEV



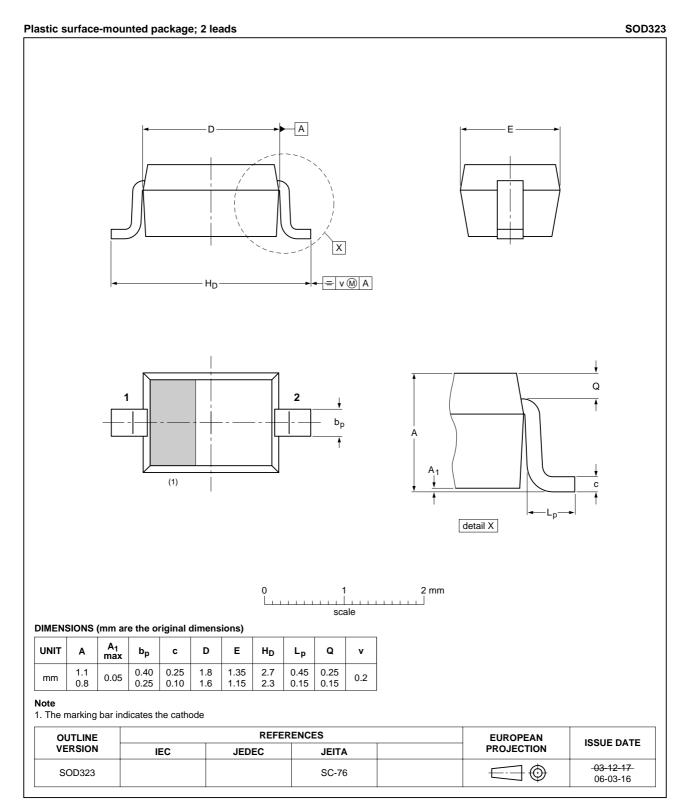


PMEGXX10BEA; PMEGXX10BEV

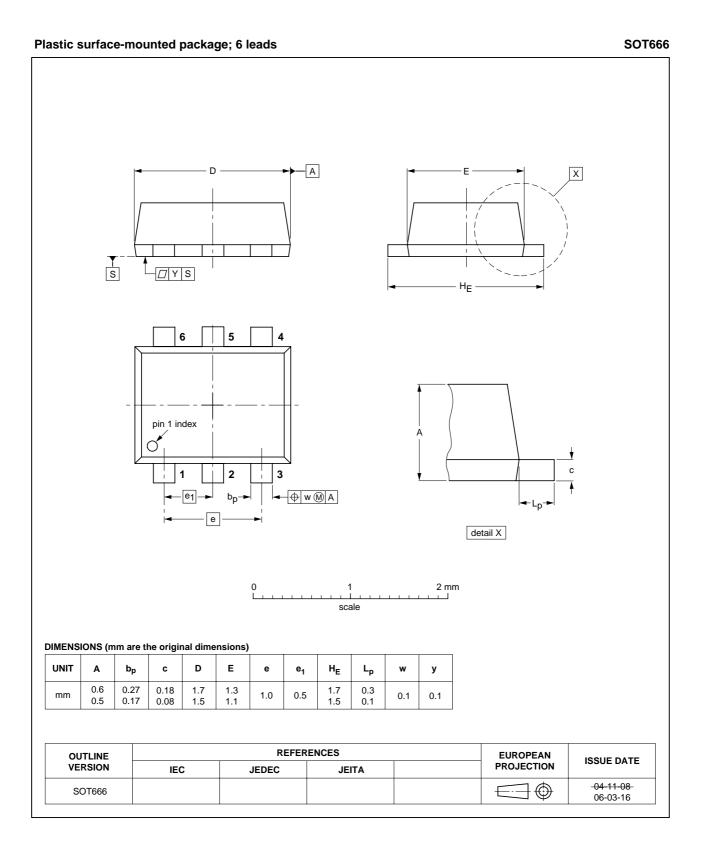
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PACKAGE OUTLINES



PMEGXX10BEA; PMEGXX10BEV



PMEGXX10BEA; PMEGXX10BEV

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Contact information

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